

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP721F

OFFICE MACHINE
SWITCHING POWER SUPPLY

Unit in mm

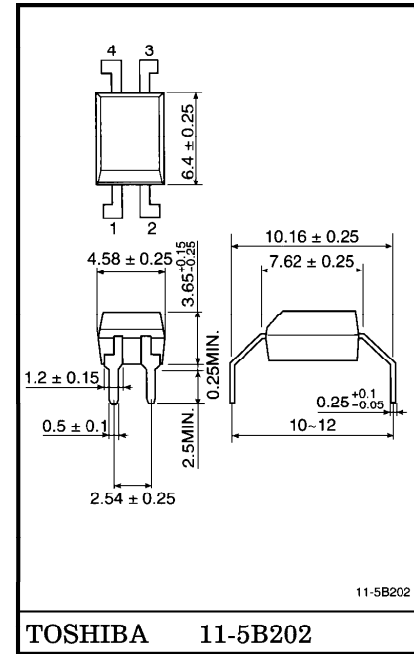
The TOSHIBA TLP721F consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a four lead plastic DIP.

All parameters are tested to the specification of TLP721.
(both condition and limits)

- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 50% (Min.)
Rank GB : 100% (Min.)

	MADE IN JAPAN	MADE IN THAILAND
UL Recognized	E67349 *1	E152349 *1
BSI Approved	7364, 7365 *2	7364, 7365 *2
SEMKO Approved	9325163 *3 9522142 *3	9609169 *4

- *1 UL1577
- *2 BS EN60065 : 1994, BS EN60950 : 1992
- *3 SS EN4330784
- *4 SS EN60950



TOSHIBA 11-5B202

Weight : 0.28g

- Option (D4) type VDE Approved

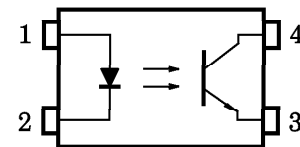
	MADE IN JAPAN	MADE IN THAILAND
VDE Approved	74285, 91835	91868
Maximum Operating Insulation Voltage	890, 1130Vpk	1130Vpk
Highest Permissible Over Voltage	6000, 8000Vpk	8000Vpk

*5 VDE0884 / 06.92

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

- Creepage Distance : 8.0mm (Min.)
Clearance : 8.0mm (Min.)
Internal Creepage Path : 4.0mm (Min.)
Insulation Thickness : 0.5mm (Min.)
- Conforming Safety Standards :
DIN 57 804.VDE0804 / 1.83
DIN IEC65 / VDE0860 / 8.81
DIN IEC380 / VDE0806 / 8.81
DIN IEC435 / VDE0805 / Draft Nov.84
DIN IEC601T1 / VDE0750T1 / 5.82
BS7002 : 1989 (EN60950)

PIN CONFIGURATION (TOP VIEW)



1. ANODE
2. CATHODE
3. EMITTER
4. COLLECTOR

961001EBC2

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